

PATENT

I hereby certify that on the date specified below, this correspondence is being sent by facsimile to Examiner Berry at 703-308-7724.

Sept. 18, 2002
Date

Wendy Thomas
Wendy Thomas

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Jérôme Ciavatti
Application No. : 10/044,307
Filed : October 26, 2001
For : DRAM BIT LINES

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SEP 18 2002

TECHNOLOGY CENTER 2800

Art Unit : 2818
Examiner : Berry
Docket No. : 859063.502
Date : September 18, 2002

Box Non-Fee Amendment
Commissioner for Patents
Washington, DC 20231

PRELIMINARY AMENDMENT

Commissioner for Patents:

Please amend the above-identified application as follows:

In the Claims:



Please cancel claims 9-17

Please add new claims 18-25 to read as follows:

18. (New) A method for manufacturing a DRAM cell structure, comprising:
forming insulating trenches on opposite sides of an active region of a substrate;
forming two inactive word lines on the insulating trenches;